

NPN SILICON SWITCHING TRANSISTOR

Qualified per MIL-PRF-19500/423

Devices

2N5581

2N5582

Qualified Level

JAN
JANTX
JANTXV

MAXIMUM RATINGS

Ratings	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current	I_C	800	mAdc
Total Power Dissipation @ $T_A = 25^{\circ}\text{C}$ ⁽¹⁾ @ $T_C = 25^{\circ}\text{C}$ ⁽²⁾	P_T	0.5 2.0	W W
Operating & Storage Junction Temperature Range	T_{op}, T_{stg}	-55 to +200	$^{\circ}\text{C}$

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for $T_A > 25^{\circ}\text{C}$

2) Derate linearly 11.43 mW/ $^{\circ}\text{C}$ for $T_C > 25^{\circ}\text{C}$



TO-46*
(TO-206AB)

*See appendix A for
package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
-----------------	--------	------	------	------

OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}$	$V_{(BR)CEO}$	50		Vdc
Collector-Base Cutoff Current $V_{CB} = 60 \text{ Vdc}$ $V_{CB} = 75 \text{ Vdc}$	I_{CBO}		10 10	ηAdc μAdc
Emitter-Base Cutoff Current $V_{EB} = 4.0 \text{ Vdc}$ $V_{EB} = 6.0 \text{ Vdc}$	I_{EBO}		10 10	ηAdc μAdc

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
DC CHARACTERISTICS ⁽³⁾				
Forward-Current Transfer Ratio $I_C = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$ $I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	2N5581 2N5582	h_{FE} h_{FE}	30 35 40 40 20 50 75 100 100 30	120 300
Collector-Emitter Saturation Voltage $I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$ $I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$	$V_{CE(sat)}$		0.3 1.0	Vdc
Base-Emitter Voltage $I_C = 150 \text{ mAdc}, I_B = 15 \text{ mAdc}$ $I_C = 500 \text{ mAdc}, I_B = 50 \text{ mAdc}$	$V_{BE(sat)}$	0.6	1.2 2.0	Vdc

DYNAMIC CHARACTERISTICS

Forward Current Transfer Ratio $I_C = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}$	2N5581 2N5582	h_{fe}	30 50	
Forward Current Transfer Ratio $I_C = 50 \text{ mAdc}, V_{CE} = 20 \text{ Vdc}, f = 100 \text{ MHz}$		$ h_{fe} $	2.5	
Output Capacitance $V_{CB} = 10 \text{ Vdc}, I_E = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$		C_{obo}	8.0	pF
Input Capacitance $V_{EB} = 0.5 \text{ Vdc}, I_C = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$		C_{ibo}	25	pF

SWITCHING CHARACTERISTICS

Turn-On Time $V_{CC} = 30 \text{ Vdc}; I_C = 150 \text{ mAdc}; I_{B1} = 15 \text{ mAdc}$	t_{on}		35	ns
Turn-Off Time $V_{CC} = 30 \text{ Vdc}; I_C = 150 \text{ mAdc}; I_{B1} = I_{B2} = 15 \text{ mAdc}$	t_{off}		300	ns

(3) Pulse Test: Pulse Width = 300 μ s, Duty Cycle $\leq$ 2.0%.